Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D T_C = +25°C
-40V	11mΩ @ V_{GS} = -10V	-35A
	15mΩ @ V_{GS} = -4.5V	-30A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. "Green" Device (Note 3)**
- **The DMP4015SK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

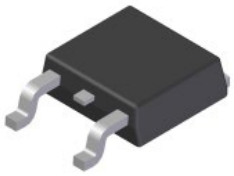
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Backlighting

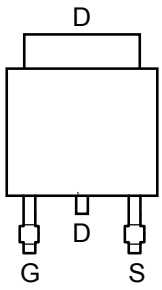
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Finish Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

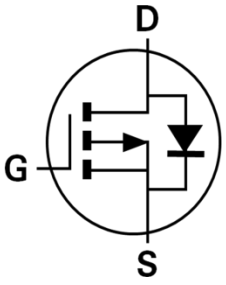
TO252 (DPAK)



Top View



Top View
Pin-Out



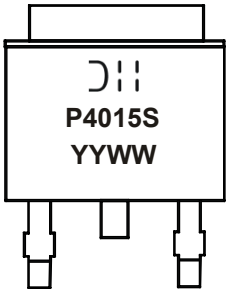
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP4015SK3Q-13	Automotive	TO252 (DPAK)	2500/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



YH = Manufacturer's Marking
P4015S = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 21 = 2021)
WW = Week (01 - 53)

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-40	V
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 5) V_{GS} = -10V	Steady State	T_C = +25°C T_C = +70°C	I_D	-35 -27	A
Continuous Drain Current (Note 5) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-14 -11	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-22 -18	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-100	A
Maximum Body Diode Forward Current (Note 5)			I_S	-5.5	A
Avalanche Current L=0.1mH			I_{AS}	-22	A
Avalanche Energy L=0.1mH			E_{AS}	242	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	3.5	W
	T_A = +70°C		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\Theta JA}$	36	°C/W
	t<10s		15	
Thermal Resistance, Junction to Case (Note 5)	Steady State	$R_{\Theta JC}$	4.5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-40	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±25V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.5	-2	-2.5	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	7	11	mΩ	V_{GS} = -10V, I_D = -9.8A
		—	9	15		V_{GS} = -4.5V, I_D = -9.8A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	26	—	S	V_{DS} = -20V, I_D = -9.8A
Diode Forward Voltage	V_{SD}	—	-0.7	-1	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	4,234	—	pF	V_{DS} = -20V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	1,036	—		
Reverse Transfer Capacitance	C_{rss}	—	526	—		
Gate Resistance	R_G	—	7.77	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	47.5	—	nC	V_{DS} = -20V, V_{GS} = -5V I_D = -9.8A
Gate-Source Charge	Q_{gs}	—	14.2	—		
Gate-Drain Charge	Q_{gd}	—	13.5	—		
Turn-On Delay Time	$t_{D(on)}$	—	13.2	—	nS	V_{GS} = -10V, V_{DD} = -20V, R_G = 6Ω, I_D = -1A
Turn-On Rise Time	t_r	—	10	—		
Turn-Off Delay Time	$t_{D(off)}$	—	302.7	—		
Turn-Off Fall Time	t_f	—	137.9	—		

Notes: 5. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.

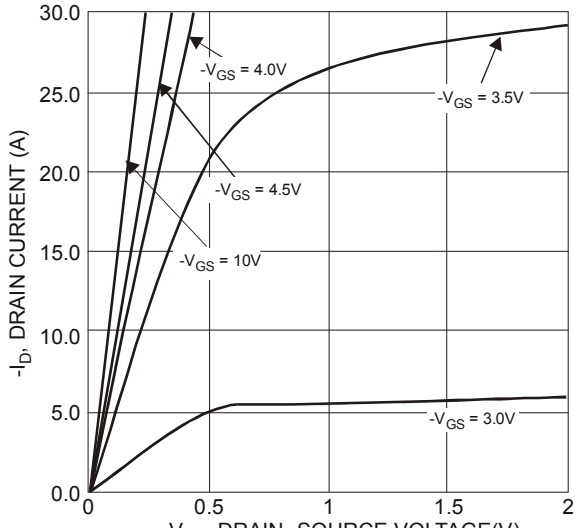


Fig. 1 Typical Output Characteristics

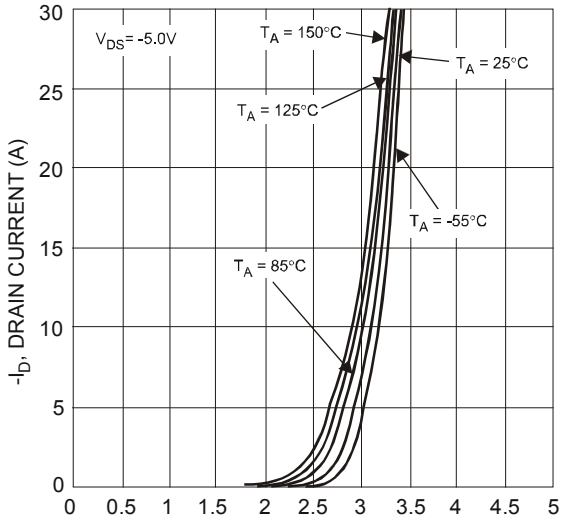


Fig. 2 Typical Transfer Characteristics

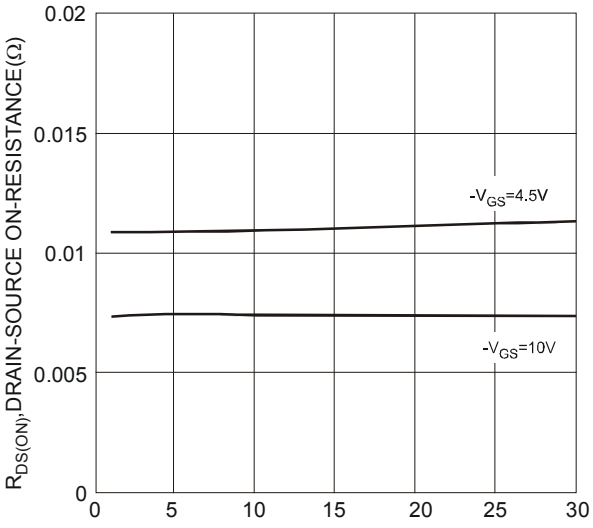


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

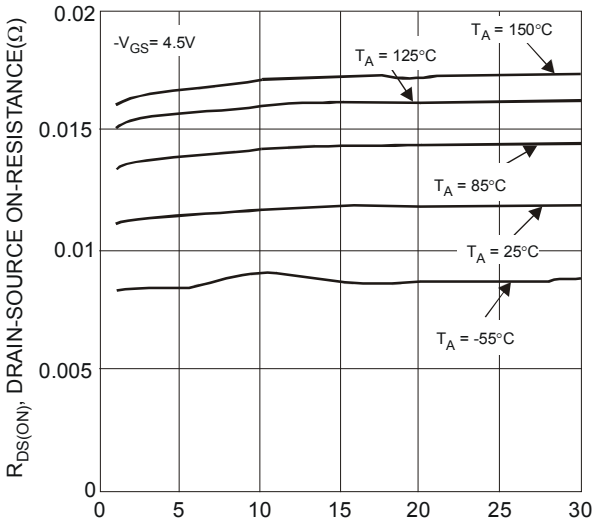


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

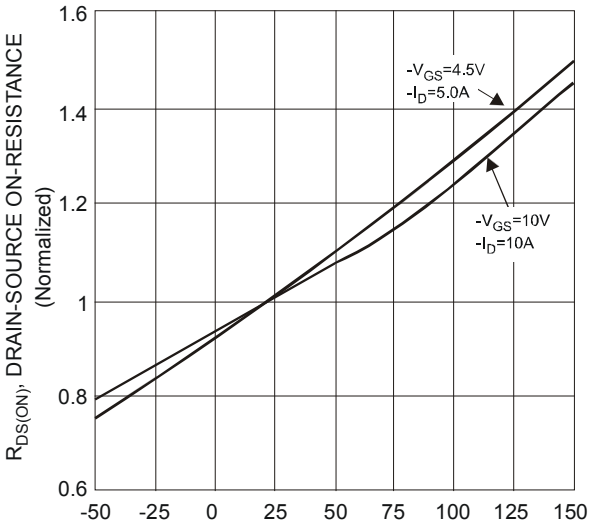


Fig. 5 On-Resistance Variation with Temperature

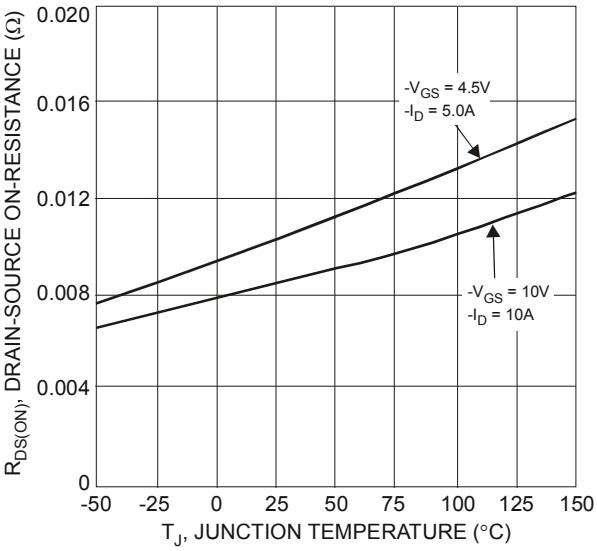


Fig. 6 On-Resistance Variation with Temperature

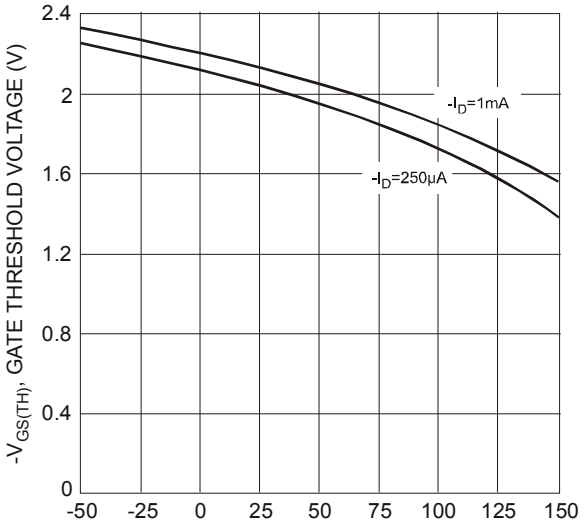


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

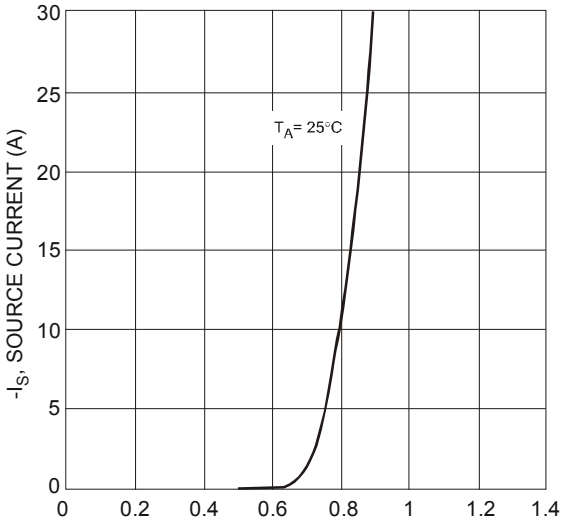


Fig. 8 Diode Forward Voltage vs. Current

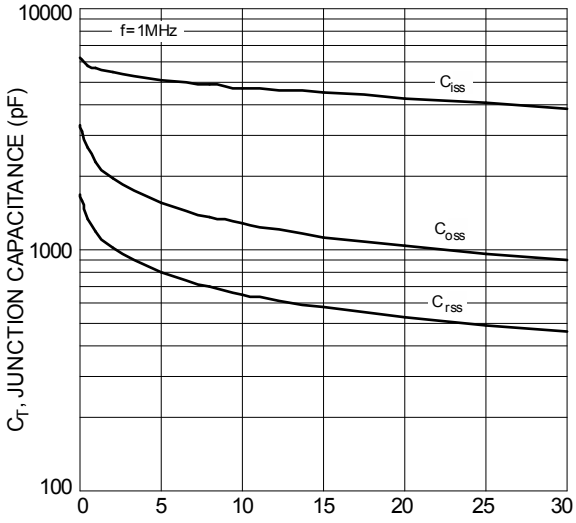


Fig. 9 Typical Junction Capacitance

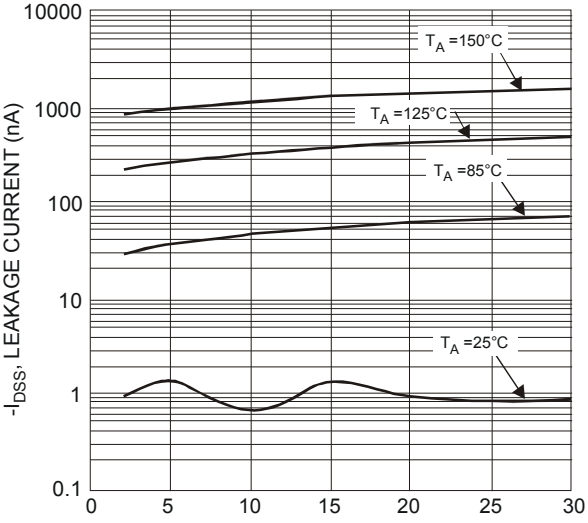


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

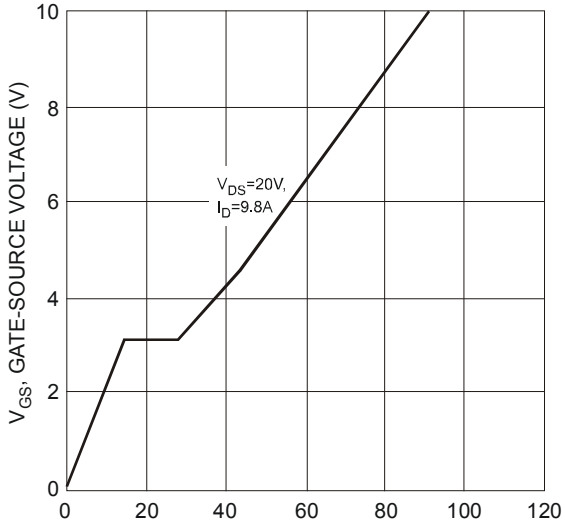


Fig. 11 Gate-Charge Characteristics

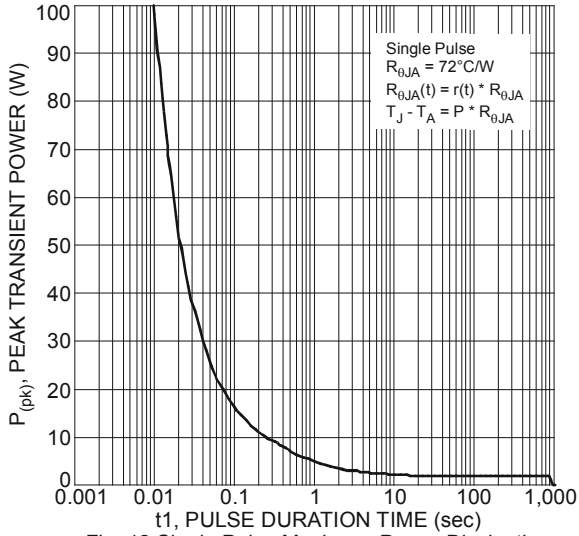


Fig. 12 Single Pulse Maximum Power Dissipation

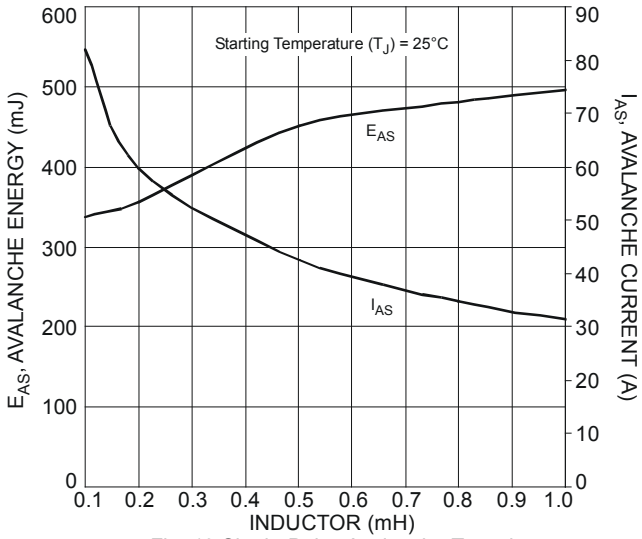


Fig. 13 Single-Pulse Avalanche Tested

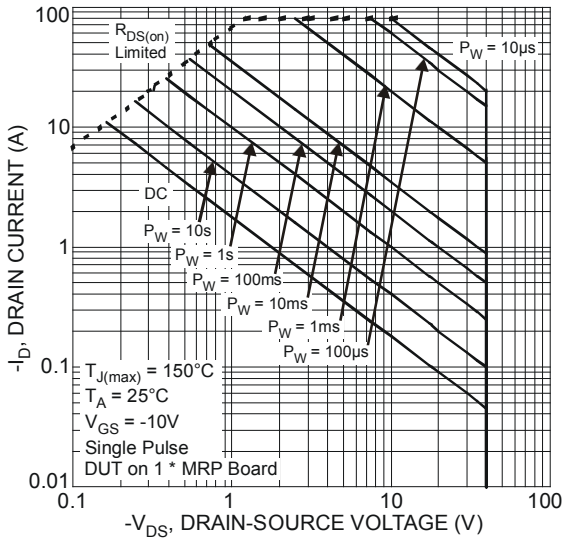


Fig. 14 SOA, Safe Operation Area

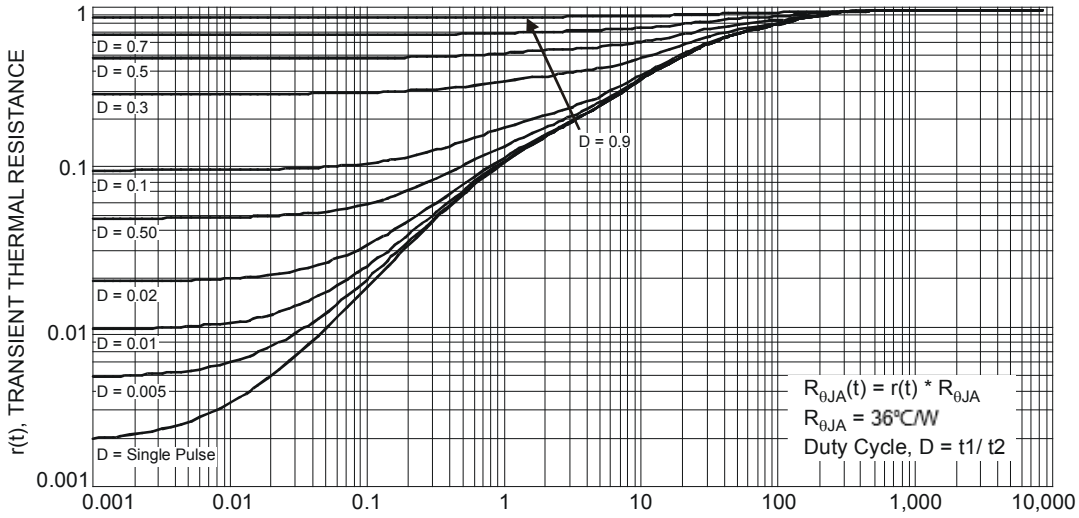
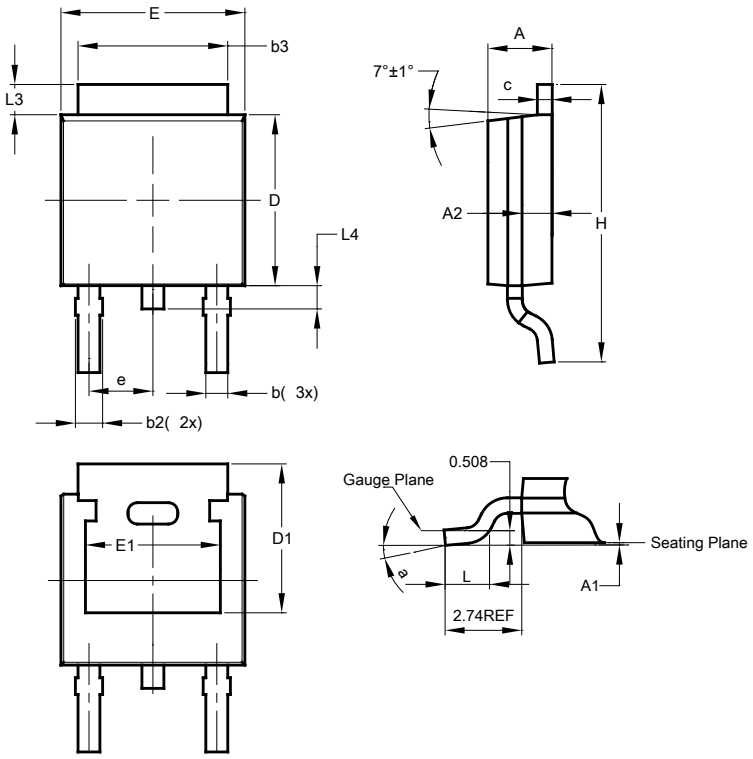


Fig. 15 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

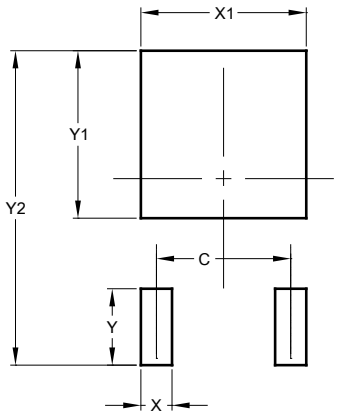


TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	—	—
e	—	—	2.286
E	6.45	6.70	6.58
E1	4.32	—	—
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	—
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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